

COMPLETE LISTING OF CLAIMS**IN ASCENDING ORDER WITH STATUS INDICATOR**

1. (Currently Amended) An apparatus for inspecting defects of devices including: a sample chamber; a movable sample stage for holding a device sample inside the sample chamber; a focused ion beam generator for irradiating a focused ion beam having a deflection range on the sample held on the sample stage; a charged particle detector for detecting secondary charged particles generated from the sample by irradiation of the focused ion beam; an image display unit for displaying an observation image A in which detected intensity of the secondary charged particles is converted into luminance signals; and a plurality of ~~conductor probes means having~~ conductor probes, to which voltage is applied, for contacting with the sample and conductor probe movement mechanisms for moving the conductor probes,

wherein the plurality of conductor probes means includes comprises:

a conductor probe means being that moves within the deflection range of the ion beam and is fixed relatively with respect to the focused ion beam generator; and

a conductor probe means being that moves in synchronization with the sample stage and is fixed relatively with respect to the sample stage.

2. (Currently Amended) The apparatus for inspecting defects of devices according to claim 1, wherein the conductor probe ~~means~~ fixed relatively ~~with respect~~ to the focused ion beam generator can be moved with a tip of the ~~conductor probe in~~ higher positioning accuracy than the conductor probe ~~means~~ fixed relatively ~~with respect~~ to the sample stage.

3. (Currently Amended) The apparatus for inspecting defects of devices according to any one of claims 1 and 2,

wherein a conductor probe movement mechanism for the conductor probe ~~means~~ fixed relatively ~~with respect~~ to the focused ion beam generator is fixed to any one of a sidewall face of the sample chamber, a ceiling face of the sample chamber and the focused ion beam generator, and

a conductor probe movement mechanism for the conductor probe ~~means~~ fixed relatively ~~with respect~~ to the sample stage is fixed to the sample stage.

4. (Currently Amended) An apparatus for inspecting defects of devices including: a sample chamber; a movable sample stage for holding a device sample inside the sample chamber; a focused ion beam generator for irradiating a focused ion beam having a deflection range on the sample held on the sample stage; a charged particle detector for detecting secondary charged particles generated from the sample by irradiation of the focused ion beam; an image display unit for displaying an observation image A in which detected intensity of the secondary charged particles is converted into luminance signals; and a plurality of conductor probes, to which voltage is applied, for contacting with the sample and conductor probe movement mechanisms for moving the conductor probes.

wherein the plurality of conductor probes comprises:

a conductor probe that moves within the deflection range of the ion beam and is fixed relative to the focused ion beam generator; and

a conductor probe that moves in synchronization with the sample stage and is fixed relative to the sample stage; and

~~The apparatus for inspecting defects of devices according to any one of claims 1 to 3, wherein the apparatus for inspecting defects of devices further wherein the apparatus includes a function of consistently ~~invariably~~ locating the tip of the conductor probe of the conductor probe means fixed relatively with respect to the focused ion beam generator within a visual field of the observation image A.~~

5. (Currently Amended) The apparatus for inspecting defects of devices according to ~~any one of claims 1 to~~ claim 4, wherein the image display unit displays an inspection area image B that indicates positions of the tips of the conductor probes on the sample.

6. (Original) The apparatus for inspecting defects of devices according to claim 5, wherein mechanical contact and non-contact of the tips of the conductor probes with the sample are displayed in the inspection area image B.

7. (Original) The apparatus for inspecting defects of devices according to any one of claims 5 and 6, wherein a state of spatial interference among the plurality of conductor probes is displayed in the inspection area image B.

8. (Currently Amended) A method of inspecting defects in devices including the steps of allowing ~~a tip of a~~ plurality of conductor probes to contact ~~with a point of voltage application on~~ a device sample being held on a sample stage, irradiating a focused ion beam from a focused ion beam generator to the sample in a state that voltage is applied from the conductor probes to the sample, and detecting wiring defects based on voltage contrasts in an image taken with a scanning ion microscope by detecting secondary charged particles generated from the sample,

wherein voltage application is carried out from ~~the~~ a conductor probe, which is held in a position fixed relatively ~~with respect~~ to the focused ion beam generator and moves within the deflection range of the ion beam, to a voltage application point necessary to be changed in relation with movement of a visual field of the scanning ion microscope, and

voltage application is carried out from ~~the~~ a conductor probe, which is held at the sample stage and moves in synchronization with the sample stage, to a voltage application point not to be changed necessarily in relation with the movement of the visual field of the scanning ion microscope.

9. (Currently Amended) The method of inspecting defects in devices according to claim 8, wherein the tip of the conductor probe held in the position fixed relatively ~~with respect~~ to the focused ion beam generator is allowed to move as linked with the visual field of the scanning ion microscope.

10. (Original) The method of inspecting defects in devices according to any one of claims 8 and 9,

wherein the position of the tip of the conductor probe is displayed as a mark superimposed on an image with the scanning ion microscope, and

the displayed position of the mark is moved relatively to the image with the scanning ion microscope to enable the position of the tip of the conductor probe to be moved corresponding to the movement.